Amendments to the Specification:

Please replace the paragraph beginning at page 8, line 22, with the following:

Figs. 12A - 12C~~12E~~ are sectional views showing a switch manufacturing process in embodiment 5 of the invention;

Please replace the paragraph beginning at page 8, line 24 with the following:

Figs. 13A - 13E~~13C~~ are sectional views showing a step modulating~~moderating~~ pattern of Figs. 12A - 12C ~~12E~~;

Please replace the paragraph beginning at page 9, line 2 with the following:

Figs. 14A - 14E are sectional views showing a switch manufacturing process to form a step modulating~~moderating~~ pattern in a shorter-side directional side surface of a signal transmitting fixed electrode, in embodiment 6 of the invention;

Please replace the paragraph beginning at page 9, line 6 with the following:

Figs. 15A - 15E are sectional views showing a switch manufacturing process to form a step modulating~~moderating~~ pattern in a longer-side directional side surface of a signal transmitting fixed electrode, in embodiment 6 of the invention;

Please replace the paragraph beginning at page 23, line 16 with the following:

Fig. 12A shows a sectional view in a manufacturing process for a switch in the case a step modulating~~moderating~~ pattern is not formed. On a high-resistance silicon substrate 1201, formed are a silicon oxide film 1202, a signal transmitting fixed electrode 1203 and an electrode-to-electrode isolating silicon oxide film 1204, by the process similar to that of the embodiment 4. Then, formed is a sacrificial layer 1205 of polyimide. Differently from the embodiment 4, the present embodiment has the sacrificial layer 1205 designed with a small width so that the sacrificial layer 1205 can be easily removed. Thereafter, an Al film 1206 is formed over the entire surface by sputtering, as shown in Fig. 12B. The sputtering

technique can stably form an Al film even in a process at a comparatively low temperature. However, there is a feature that deposition is not easy on the side surface of a step. In the evaporation technique, deposition is not easy on the side surface of a step. Meanwhile, where a CVD process is used in a low-pressure atmosphere, deposition is possible on the step side surface, but there is a limitation in application scope because of its high process temperature. Accordingly, the Al film is formed with a thickness-reduced region 1207 at a step. Thereafter, as shown in fig. 12C, a resist mask is formed in a predetermined area where a movable electrode and movable electrode driving fixed electrode are arranged. The Al is etched using the resist mask as a mask, to form a movable electrode 1208 and movable electrode driving fixed electrode 1209. Furthermore, by removing away the resist mask and sacrificial layer 1205, a capacitance reducing space 1210 is formed. On the other hand, the thickness-reduced area at the step of the sacrificial layer 1205 is left, as it is, as a strength-deficient region 1211 of the movable electrode driving fixed electrode 1209.

Please replace the paragraph beginning at page 24, line 22 with the following:

Fig. 13 shows a sectional view in a manufacturing process for a switch in the case a step modulating~~moderating~~ pattern for step coverage compensation is formed. In Fig. 13A, a silicon oxide film 1202, a signal transmitting fixed electrode 1203 and an electrode-to-electrode isolating silicon oxide film 1204 are formed on a high-resistance silicon substrate 1201, by a process similar to that of the embodiment 4. Next, as shown in Fig. 13B, photoresist is spin-coated. This is exposed to light and developed, and then baked on a hot plate, thereby forming a step modulating~~moderating~~ pattern 1212 in a predetermined area. The step-modulating~~moderating~~ pattern 1212 is formed in such a position and film thickness that a step formed by a movable electrode driving fixed electrode in a later process and by the sacrificial layer can be divided.

Please replace the paragraph beginning at page 25, line 10 with the following:

Subsequently, as shown in Fig. 13C, formed is a sacrificial layer 1205 of polyimide. The step-modulating~~moderating~~ pattern 1212 exists outside of the sacrificial-layer end surface 1213. In the absence of the step modulating~~moderating~~

pattern 1212, a step having a length from a sacrificial layer 1205 surface to the silicon oxide film 1202 surface is formed at the end surface of the sacrificial layer. On the contrary, by the step modulating~~moderating~~ pattern 1212, the step is divided into two, i.e. a step from the sacrificial layer surface to the step modulating ~~moderating~~ pattern surface and a step from the step modulating~~moderating~~ pattern surface to the silicon oxide film surface. This makes it possible to prevent a great step from being formed at one point. Thereafter, as shown in Fig. 13D, an Al film 1206 is formed over the entire surface by sputtering. Furthermore, as shown in Fig. 13E, a resist mask is formed in a predetermined area where a movable electrode and a movable electrode driving fixed electrode are arranged, by a process similar to that of the embodiment 4. The Al is etched using the resist mask as a mask, to form a movable electrode 1208 and a movable electrode driving fixed electrode 1209. Furthermore, by removing the resist mask, the sacrificial layer and the step modulating~~moderating~~ pattern, a capacity reducing space 1210 is formed. Because the step in the sacrificial layer for the capacity reducing space is moderated by the both of the sacrificial layer and the step modulating~~moderating~~ pattern, in the movable electrode driving fixed electrode 1110, a strength deficient region of an extremely small film thickness is not formed.

Please replace the paragraph beginning at page 26, line 23 with the following:

Incidentally, although as the step modulating~~moderating~~ pattern of the embodiment, photoresist is used, polyimide may be used without any problem. Furthermore, in the embodiment, as the step modulating~~moderating~~ pattern the material to be removed away by a sacrificial layer removal process is used. In the case of a material not to be removed by a sacrificial later removal process, the movable electrode driving fixed electrode has a further increased strength.

Please replace the paragraph beginning at page 27, line 8 with the following:

Fig. 14 shows a sectional view in a manufacturing process for a switch in the case a step modulating~~moderating~~ pattern is formed on the both sides of the signal transmitting fixed electrode in a shorter-side direction thereof, showing a section along line A-A' in Fig. 2. In Fig. 14A, a silicon oxide film 102, a signal transmitting fixed electrode 105 and an electrode-to-electrode isolating silicon oxide film 1304 are

formed on a high-resistance silicon substrate 101, by a process similar to that of the embodiment 4.

Please replace the paragraph beginning at page 28, line 11 with the following:

Furthermore, as shown in Fig. 14E, a resist mask is formed in a predetermined area where a movable electrode is arranged, by the process similar to that of the embodiment 4. The Al is etched using the resist mask as a mask, to form a movable electrode 1309. Furthermore, by removing away the resist mask, sacrificial layer and step modulating~~moderating~~ pattern, a capacitance reducing space 1310 is formed. Because the step in the sacrificial layer for the capacity reducing space is moderated by the both of the sacrificial layer and the step modulating~~moderating~~ pattern, the movable electrode 1309 is not formed with a strength deficient region of an extremely small film thickness. Incidentally, although the step modulating~~moderating~~ pattern in this embodiment was formed of polyimide, it is not problematic, similarly to embodiment 5 if is left after a sacrificial layer removal process.

Please replace the paragraph beginning at page 29, line 1 with the following:

Fig. 15 shows a sectional view in a manufacturing process for a switch in the case a step modulating~~moderating~~ pattern is formed on the both sides of the signal transmitting fixed electrode in a longer-side direction thereof, showing a section along line B-B' in Fig. 2. In Fig. 15A, a silicon oxide film 102, a signal transmitting fixed electrode 105 and an electrode-to-electrode isolating silicon oxide film 1304 are formed on a high-resistance silicon substrate 101, by a process similar to that of embodiment 4.

Please replace the paragraph beginning at page 29, line 10 with the following:

Next, as shown in Fig. 15B, photoresist is spin-coated. After exposure to light and development, baking is done on a hot plate, thereby forming a step modulating ~~moderating~~ pattern 1305 on the both sides of the signal transmitting fixed electrode in a longer-side direction thereof. The step modulating~~moderating~~ pattern 1305 is formed beneath convex and concave parts in a movable electrode side surface and

concave and convex parts in a movable electrode driving fixed electrode which are formed in the later process. The step modulating~~moderating~~ pattern is formed in a film thickness of adding together of the film thickness of the signal transmitting fixed electrode and the film thickness of the electrode-to-electrode isolating silicon oxide film, in other words, the step modulating~~moderating~~ pattern has the same height with that of the electrode-to-electrode isolating silicon oxide film with respect to a substrate surface.

Please replace the paragraph beginning at page 29, line 25 with the following:

Subsequently, as shown in Fig. 15C, a polyimide sacrificial layer 1306 is formed. By forming the step modulating~~moderating~~ pattern 1305 in a film thickness of adding together of the film thickness of the signal transmitting fixed electrode 105 and the film thickness of the electrode-to-electrode isolating silicon oxide film 1304, the sacrificial layer has a constant surface height with respect to the substrate surface in the area from the signal transmitting fixed electrode to nearly the end surface of the step modulating~~moderating~~ pattern 1305.

Please replace the paragraph beginning at page 30, line 9 with the following:

Thereafter, as shown in Fig. 15D, an Al film 1308 is formed on the entire surface by a sputtering process. Furthermore, by a process similar to that of embodiment 4, a photoresist mask 1311 for forming a movable electrode and a photoresist mask 1312 for forming a movable electrode driving fixed electrode are formed in a predetermined position where the movable electrode and movable electrode driving fixed electrode are arranged. The mask for forming the movable electrode driving fixed electrode is partly positioned above the step modulating ~~moderating~~ pattern 1305, to constitute a region 1313 where convex and concave parts of the movable electrode driving fixed electrode are formed. This has the same height as the surface of the movable electrode mask, due to the step modulating ~~moderating~~ pattern 1305.

Please replace the paragraph beginning at page 31, line 8 with the following:

Subsequently, as shown in fig. 15E, the resist mask is used as a mask, to etch Al thereby forming a movable electrode 1309 and movable electrode driving fixed electrode 1314. Thereafter, by removing the resist mask, the sacrificial layer and the step modulating~~moderating~~ pattern, a capacitance reducing space 1310 is formed. In this manner, by applying the present embodiment, a finer pattern can be formed in respect of the convex and concave parts in the movable electrode side surface and convex and concave parts in the movable electrode driving fixed electrode.